

**AMENDMENTS TO THE CLAIMS**

Please cancel Claim 21.

1. (Previously Presented) A process of growing a thin film of  $\text{Al}_2\text{O}_3$  on a substrate having a surface in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising, in order:
  - exposing the substrate in the reaction chamber to gaseous trimethyl aluminum (TMA), such that more than one monolayer of TMA forms on the substrate surface;
  - stopping provision of the gaseous TMA;
  - removing gaseous TMA from the reaction chamber;
  - exposing the substrate in the reaction chamber to atomic oxygen; and
  - removing atomic oxygen from the reaction chamber;wherein in each cycle more than one monolayer of  $\text{Al}_2\text{O}_3$  is formed.
2. (Previously Presented) The process of Claim 1, wherein in each cycle a layer of  $\text{Al}_2\text{O}_3$  3 Å thick is formed.
3. (Previously Presented) The process of Claim 1, wherein the atomic oxygen is generated remotely in a radical generator.
4. (Original) The process of Claim 1, wherein the process is carried out at room temperature.
5. - 21. (Cancelled)